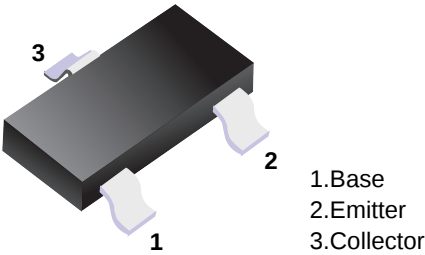


2SC3265

NPN Transistors

Features

- High DC current gain
- Low saturation voltage
- Complementary to 2SA1298



Simplified outline(SOT-23)

Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	VCBO	30	V
Collector - Emitter Voltage	VCEO	25	
Emitter - Base Voltage	VEBO	5	
Collector Current - Continuous	IC	800	mA
Base Current	IB	160	
Collector Power Dissipation	PC	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	Tstg	-55 to 150	

Electrical Characteristics Ta = 25°C

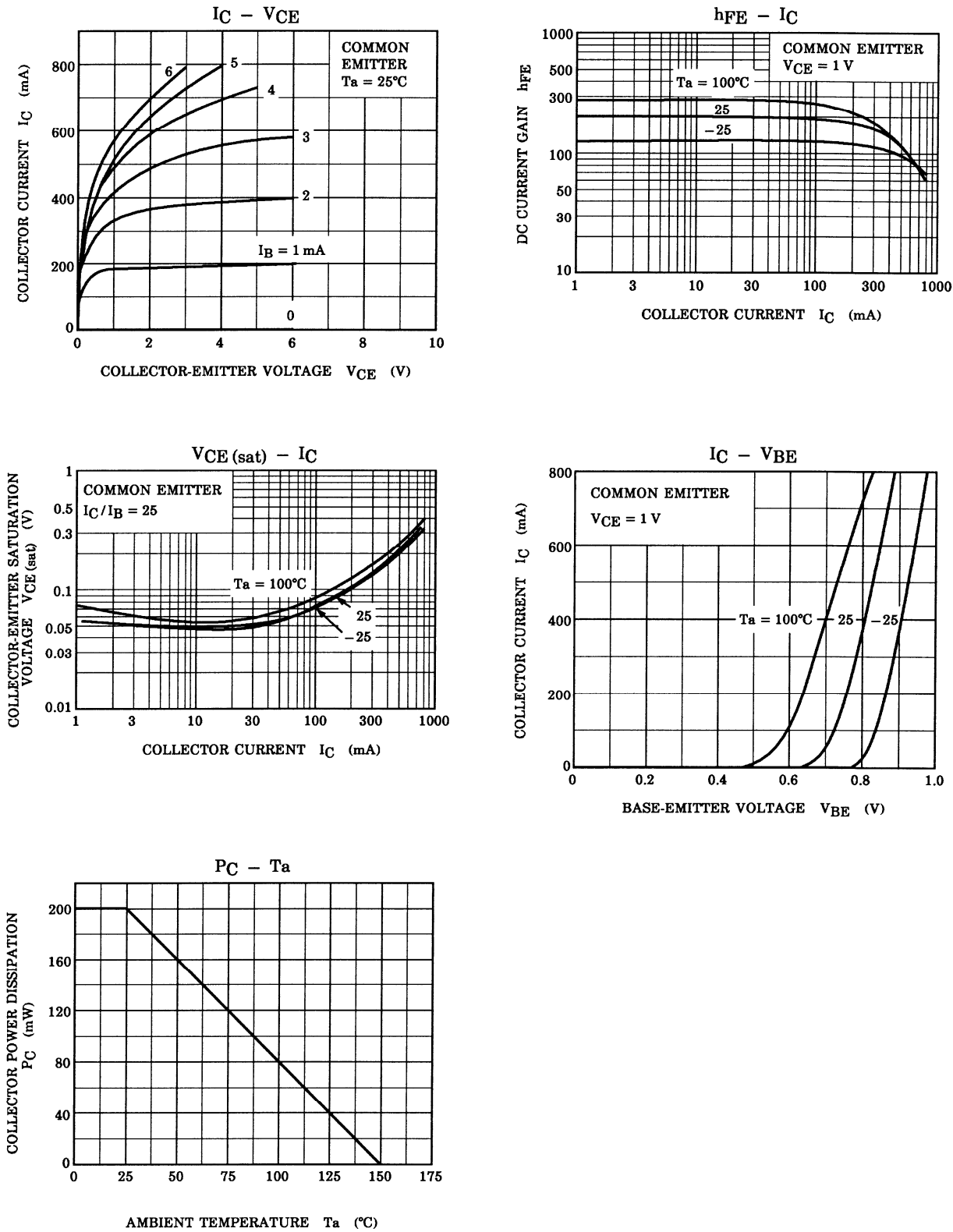
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	VCBO	IC= 100 μA, IE= 0	30			V
Collector- emitter breakdown voltage	VCEO	IC= 10 mA, IB= 0	25			
Emitter - base breakdown voltage	VEBO	IE= 100 μA, IC= 0	5			
Collector-base cut-off current	ICBO	VCB= 30 V, IE= 0			0.1	uA
Emitter cut-off current	IEBO	VEB= 5V, IC=0			0.1	
Collector-emitter saturation voltage	VCE(sat)	IC= 500 mA, IB=20 mA			0.4	V
Base - emitter saturation voltage	VBE(sat)	IC= 500 mA, IB=20 mA		0.72	1	
Base - emitter voltage	VBE	VCE= 1V, IC= 10mA	0.5		0.8	
DC current gain	hFE	VCE= 1V, IC= 100mA	100		320	
		VCE= 1V, IC= 800mA	40			
Collector output capacitance	Cob	VCB= 10V, IE=0, f=1MHz		13		pF
Transition frequency	fT	VCE= 5V, IC= 10mA		120		MHz

Classification of hfe(1)

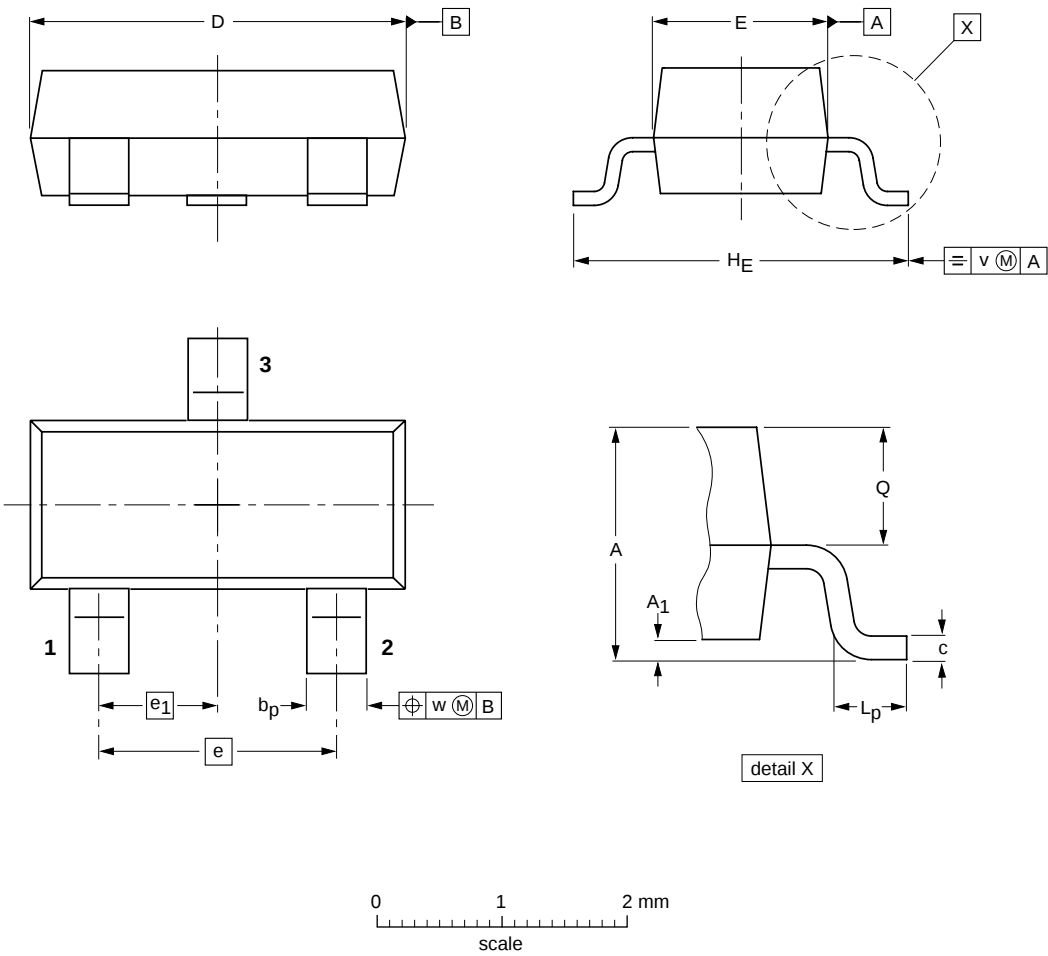
Type	2SC3265-O	2SC3265-Y
Range	100-200	160-320
Marking	EO	EY

2SC3265

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1